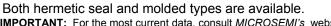


1N5907 and 1N5908

1500 WATT LOW VOLTAGE TRANSIENT VOLTAGE SUPPRESSOR

DESCRIPTION

This pair of unidirectional low voltage Transient Voltage Suppressor (TVS) devices for the 1N5907 and 1N5908 JEDEC registrations with different packages have the same high Peak Pulse Power rating of 1500 W with extremely fast response times. The 1N5907 is available in a military qualified version as described in the Features section herein. They are most often used for protecting against transients from inductive switching environments, induced RF effects, or induced secondary lightning effects as found in surge levels of IEC61000-4-5 described herein. They are also very successful in protecting airborne avionics and electrical systems when low voltage is required. Since their response time is virtually instantaneous, they can also protect from ESD and EFT per IEC61000-4-2 and IEC61000-4-4.



IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

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FEATURES

- Unidirectional TVS series for thru-hole mounting
- Suppresses transients up to 1500 watts @ 10/1000 μs (Figure 1) in less than 100 pico seconds
- Low working voltage (V_{WM}) of 5 V
- Hermetic sealed DO-13 metal package for 1N5907 and plastic "Case 1" for 1N5908
- JAN/TX/TXV military qualification available for 1N5907 per MIL-PRF-19500/500 by adding JAN, JANTX, or JANTXV prefix, e.g. JANTXV1N5907
- Surface mount equivalent packages also available as SMCJ5.0 or SMCG5.0 in separate data sheet (consult factory for other surface mount options)

MAXIMUM RATINGS

- 1500 Watts for 10/1000 μs at lead temperature (T_L) 25°C (See Figs. 1, 2, and 4) with repetition rate of 0.01% or less*
- Operating & Storage Temperatures: -65° to +175°C for 1N5907 and
 - -65° to +150°C for 1N5908
- THERMAL RESISTANCE (junction to lead): 50°C/W for 1N5907 or 22°C/W for 1N5908 at 0.375 inches (10 mm) from body
- THERMAL RESISTANCE (junction to ambient): 110 °C/W for 1N5907, or 82 °C/W for 1N5908 when mounted on FR4 PC board with 4 mm² copper pads (1 oz) and track width 1 mm, length 25 mm
- DC Power Dissipation* (1N5907): 1 Watt at T_L ≤125°C 3/8" (10 mm) from body, or 1 Watt at T_A ≤+65°C when mounted on FR4 PC board as described for thermal resistance junction to ambient
- DC Power Dissipation* (1N5908): 5 Watts at T_L \leq +40°C 3/8" (10 mm) from body, or 1.52 Watts at T_A = +25°C when mounted on FR4 PC board as described for thermal resistance junction to ambient
- Forward surge current: 200 A for 8.3ms half-sine wave at $T_{\rm A}$ = +25°C
- Solder Temperatures: 260 ° C for 10 s (maximum)

DO-13 (DO-202AA) CASE 1

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APPLICATIONS / BENEFITS
Protection from switching transients and induced RF Protects TTL, ECL, DTL, MOS, MSI, and other integrated circuits requiring 5.0 V or lower power supplies
Protection from ESD and EFT per IEC 61000-4-2 and IEC 61000-4-4
Secondary lightning protection per IEC61000-4-5 with 42 Ohms source impedance: Class 1 thru 4
Secondary lightning protection per IEC61000-4-5 with 12 Ohms source impedance: Class 1 thru 4
Secondary lightning protection per IEC61000-4-5 with 2 Ohms source impedance: Class 2 & 3
1N5907 Inherently radiation hard as described in Microsemi MicroNote 050

MECHANICAL AND PACKAGING

- CASE (1N5907): DO-13 (DO-202AA) welded hermetically sealed metal and glass
- Case (1N5908): "Case 1" Void Free transfer molded thermosetting epoxy body meeting UL94V-0
- FINISH: External metal surfaces are Tin-Lead (Sn-Pb) plated and solderable per MIL-STD-750 method 2026
- POLARITY: Polarity indicated by diode symbol or cathode band (cathode connected to case for 1N5907)
- MARKING: Part number and polarity symbol
- WEIGHT: 1.4 grams. (Approx)
- TAPE & REEL option: Standard per EIA-296 (add "TR" suffix to part number)
- See package dimension on last page

* TVS devices are not typically used for dc power dissipation and are instead operated at or less than their rated standoff voltage (V_{WM}) except for transients that briefly drive the device into avalanche breakdown (V_{BR} to V_C region).

Sicrosemi
SCOTTSDALE DIVISION

1N5907 and 1N5908

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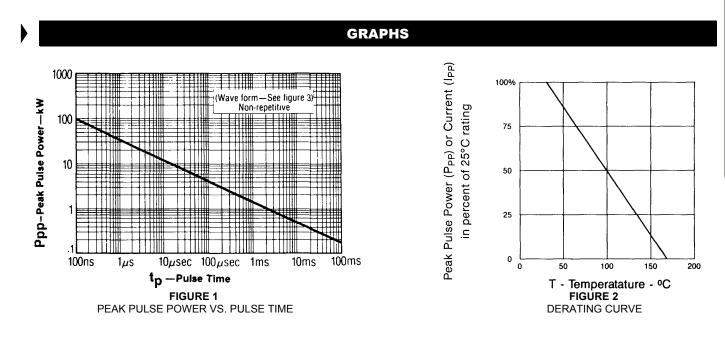
ELECTRICAL CHARACTERISTICS @ 25°C

JEDEC Type No.	Reverse Standoff Voltage V _{WM} (NOTE 1)	Minimum Breakdown Voltage V _(BR) @ 1 mA	Maximum Standby Current I _D @ V _{₩M}	Maximum Clamping Voltage V _C @ I _{PP1} (FIG. 3)	Peak Pulse Current I _{PP1} (FIG. 3)	Maximum Clamping Voltage V _C @ I _{PP2} (FIG. 3)	Peak Pulse Current I _{PP2} (FIG. 3)	Maximum Clamping Voltage V _C @ I _{PP3} (FIG. 3)	Peak Pulse Current I _{PP3} (FIG. 3)
	Volts	Volts	μA	Volts	Amps	Volts	Amps	Volts	Amps
1N5907*	5.0	6.0	300	7.6	30	8.0	60	8.5	120
1N5908	5.0	6.0	300	7.6	30	8.0	60	8.5	120

* Also available in military qualified types with a JAN, JANTX, or JANTXV prefix per MIL-PRF-19500/500.

NOTE 1: A TVS is normally selected according to the reverse "Standoff Voltage" V_{WM} which should be equal to or greater than the dc or continuous peak operating voltge level.

	SYMBOLS & DEFINITIONS
Symbol	Definition
Vwm	Standoff Voltage: Applied Reverse Voltage to assure a nonconductive condition. (See Note 1 above)
V _(BR)	Breakdown Voltage: This is the Breakdown Voltage the device will exhibit at 25°C
V _C	Maximum Clamping Voltage: The maximum peak voltage appearing across the TVS when subjected to the peak pulse current in a one millisecond time interval. The peak pulse voltage is the combination of voltage rise due to both the series resistance and thermal rise and positive temperature coefficient ($\alpha_{V(BR)}$)
IPP	Peak Pulse Current: The peak current during the impulse (See Figure 2)
P _{PP}	Peak Pulse Power: The pulse power as determined by the product of V_C and I_{PP}
Ι _D	Standby Current: The current at the standoff voltage (V _{WM})
I _(BR)	Breakdown Current: The current used for measuring Breakdown Voltage (V(BR))



1N5907 thru 1N5908



1N5907 and 1N5908

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